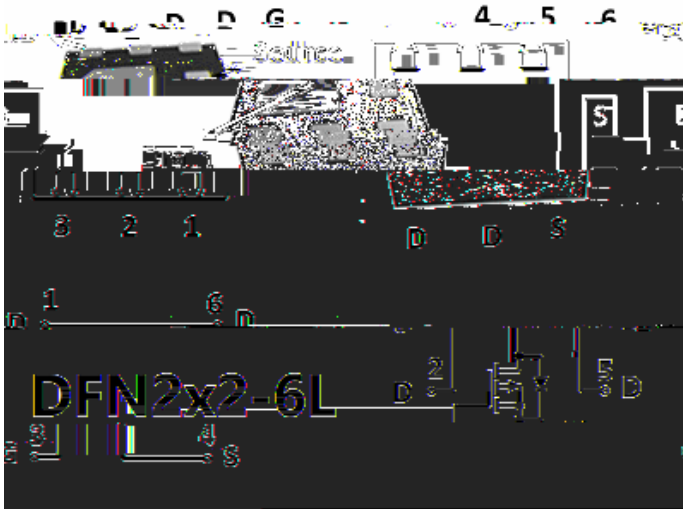




- V_{DS} -20V
- I_D -7A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) 36.5mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) 46.5mohm
- $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 60.5mohm

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

- Battery protection
- Power management
- Load switch

($T_A=25$ unless otherwise noted)

Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_C=25$ @ Steady State	I_D	-7	A
	$T_C=70$ @ Steady State		-5.6	
Pulsed Drain Current ^A		I_{DM}	-28	A
Total Power Dissipation @ $T_C=25$ ^C		P_D	2.2	W

Thermal Resistance Junction-to-Ambient @ Steady State ^D

$R_{\theta JA}$

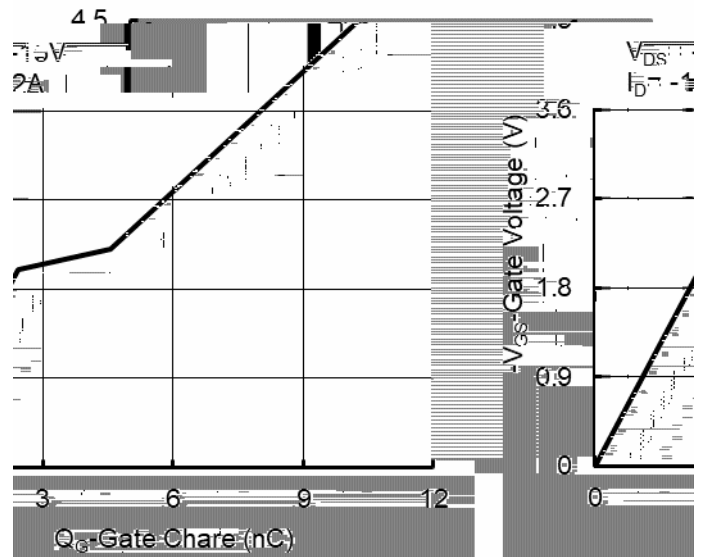
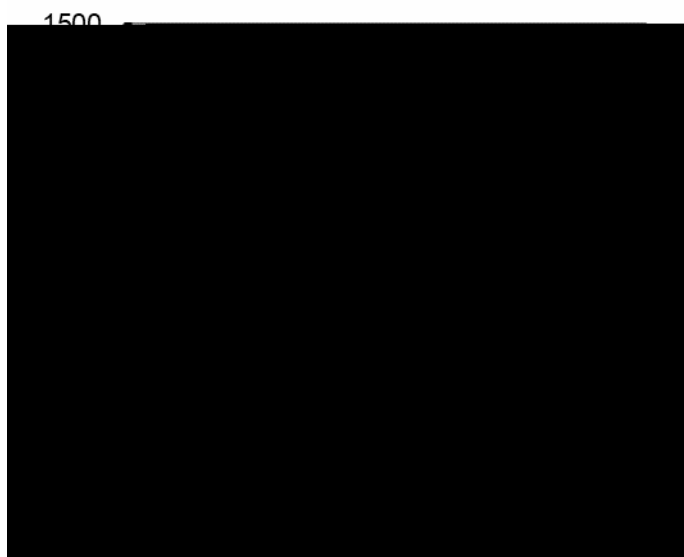
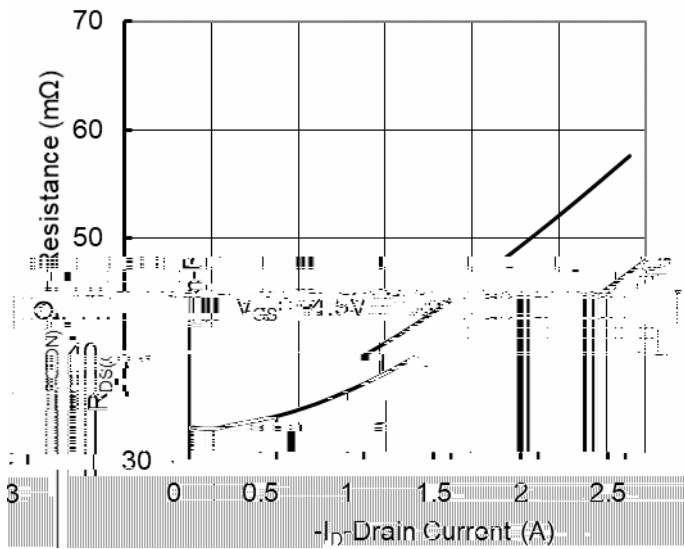
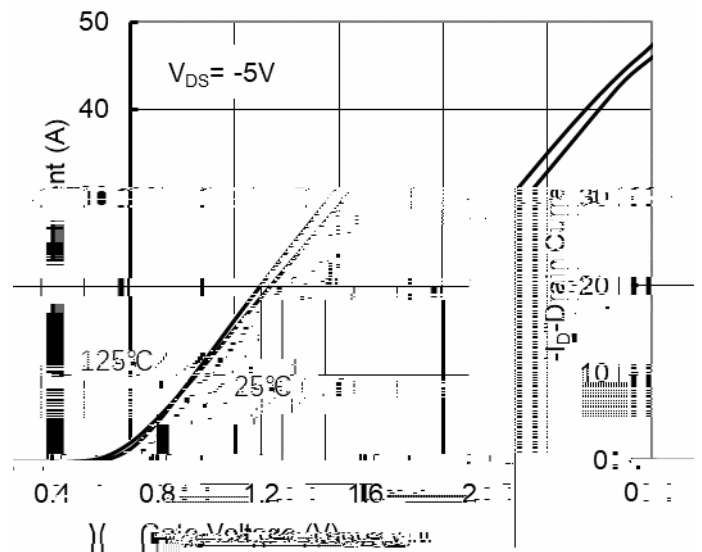
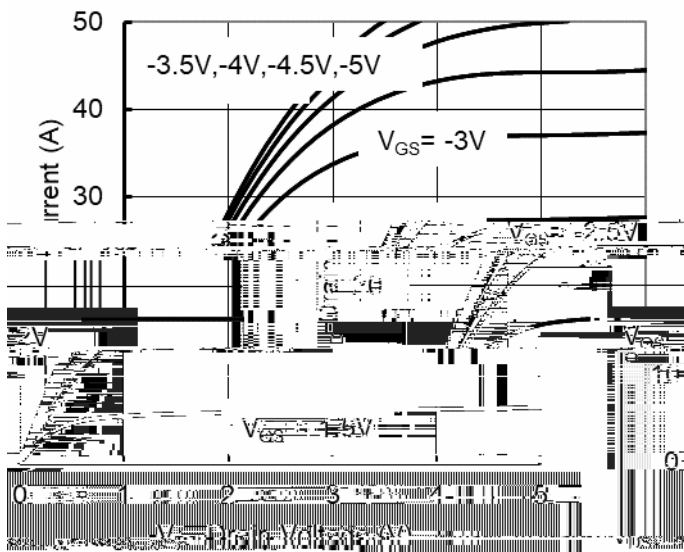
(Example)

YJQ4666B	F1	..G66B	3000	30000	120000	7 " reel

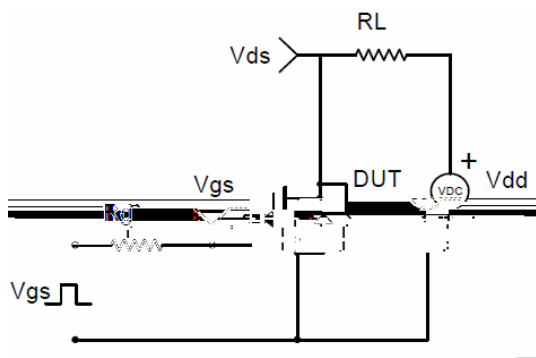


■

(T_J=25









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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, weapons, radar equipment, aircraft, ships, etc.)